

ABSTRACT OF THE DISCLOSURE

Arrangements are provided to effectively prevent
wire disconnection generated due to an increase of heat
5 applied to a semiconductor integrated circuit device. The
semiconductor integrated circuit device is structured such
that a metal layer containing a Pd layer is provided in a
portion to which a connecting member having a conductivity
is connected, and an alloy layer having a melting point
10 higher than that of an Sn-Pb eutectic solder and containing
no Pb as a main composing metal is provided outside a
portion molded by a resin. Further, a metal layer in which
a thickness in a portion to which the connecting member
having the conductivity is adhered is equal to or more than
15 10 μm is provided in the connecting member.